# Hong Jin Kim

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/11648995/publications.pdf

Version: 2024-02-01

| 17 | 206 | 1163117<br>8 | 1125743<br>13 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 18 | 18 | 18 | 148 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Effect of brush cleaning on defect generation in post copper CMP. Microelectronic Engineering, 2022, 261, 111808. | 2.4 | 1 |
| 2 | Storage Temperature Effects on the Slurry Health Parameters and SiO<sub>2</sub> Removal Rates during Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2021, 10, 104002. | 1.8 | 1 |
| 3 | Effect of Controlling Abrasive Size in Slurry for Tungsten Contact CMP Process. ECS Journal of Solid State Science and Technology, 2019, 8, P3206-P3211. | 1.8 | 10 |
| 4 | Study on the Mechanism of Nano-Flake Defect during Tungsten Contact Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2018, 7, P175-P179. | 1.8 | 9 |
| 5 | Abrasive for Chemical Mechanical Polishing. , 2018, , . | | 5 |
| 6 | A New Approach to the Formation Mechanism of Tungsten Void Defect in Chemical Mechanical Polishing. ECS Journal of Solid State Science and Technology, 2018, 7, P693-P697. | 1.8 | 9 |
| 7 | Brush cleaning effect on tugnsten voids defect in chemical mechanical polishing: CFM: Contamination free manufacturing. , 2018, , . | | 2 |
| 8 | Effect of Reactive Ion Etch on the Polishing Selectivity during Silicon Nitride Chemical Mechanical Polishing for Sub-10 nm Logic Device. ECS Journal of Solid State Science and Technology, 2017, 6, P101-P104. | 1.8 | 4 |
| 9 | Effect of post CMP in-situ cleaning and its optimization on the defect improvement: CFM: Contamination free manufacturing. , 2016, , . | | 7 |
| 10 | Metal Flake Defect and Its Formation Mechanism during Replacement Metal Gate CMP Process. ECS Journal of Solid State Science and Technology, 2016, 5, P637-P640. | 1.8 | 6 |
| 11 | Study of the cross contamination effect on post CMP in situ cleaning process. Microelectronic Engineering, 2015, 136, 36-41. | 2.4 | 46 |
| 12 | Effect of Brush Treatment and Brush Contact Sequence on Cross Contaminated Defects during CMP in-situ Cleaning. Journal of the Korean Society of Tribologists and Lubrication Engineers, 2015, 31, 239-244. | 0.1 | 11 |
| 13 | Effects of Pad Temperature on the Chemical Mechanical Polishing of Tungsten. ECS Journal of Solid State Science and Technology, 2014, 3, P310-P314. | 1.8 | 9 |
| 14 | Effect of pad surface roughness on material removal rate in chemical mechanical polishing using ultrafine colloidal ceria slurry. Electronic Materials Letters, 2013, 9, 155-159. | 2.2 | 15 |
| 15 | First observation on the feasibility of scratch formation by padâ€“particle mixture in CMP process. Applied Surface Science, 2012, 258, 8298-8306. | 6.1 | 28 |
| 16 | MICROSTRUCTURES PRODUCED BY DYNAMIC FRICTION. , 2008, , . | | 0 |
| 17 | MD Simulations of Microstructure Evolution during High-Velocity Sliding between Crystalline Materials. Tribology Letters, 2007, 28, 299-306. | 2.6 | 40 |